DATASHEET

EL5211T

RENESAS

NOT RECOMMENDED FOR NEW DESIGNS NO RECOMMENDED REPLACEMENT contact our Technical Support Center at 1-888-INTERSIL or www.intersil.com/tsc

60MHz Rail-to-Rail Input-Output Operational Amplifier

The EL5211T is a high voltage rail-to-rail input-output amplifier with low power consumption. The EL5211T contains two amplifiers. Each amplifier exhibits beyond the rail input capability, rail-to-rail output capability and is unity gain stable.

The maximum operating voltage range is from 4.5V to 19V. It can be configured for single or dual supply operation, and typically consumes only 3mA per amplifier. The EL5211T has an output short circuit capability of \pm 300mA and a continuous output current capability of \pm 65mA.

The EL5211T features a high slew rate of 100V/µs, and fast settling time. Also, the device provides common mode input capability beyond the supply rails, rail-to-rail output capability, and a bandwidth of 60MHz (-3dB). This enables the amplifiers to offer maximum dynamic range at any supply voltage. These features make the EL5211T an ideal amplifier solution for use in TFT-LCD panels as a V_{COM} driver or static gamma buffer, and in high speed filtering and signal conditioning applications. Other applications include battery power and portable devices, especially where low power consumption is important.

The EL5211T is available in a thermally enhanced 8 Ld HMSOP package, and a thermally enhanced 8 Ld DFN package. Both feature a standard operational amplifier pinout. The device operates over an ambient temperature range of -40° C to $+85^{\circ}$ C.

Features

- 60MHz (-3dB) Bandwidth
- 4.5V to 19V Maximum Supply Voltage Range
- 100V/ μs Slew Rate
- 3mA Supply Current (per Amplifier)
- ±65mA Continuous Output Current
- ±300mA Output Short Circuit Current
- Unity-gain Stable
- · Beyond the Rails Input Capability
- Rail-to-rail Output Swing
- Built-in Thermal Protection
- -40°C to +85°C Ambient Temperature Range
- Pb-Free (RoHS Compliant)

Applications* (see page 13)

- TFT-LCD Panels
- V_{COM} Amplifiers
- Static Gamma Buffers
- Drivers for A/D Converters
- Data Acquisition
- Video Processing
- Audio Processing
- Active Filters
- Test Equipment
- Battery-powered Applications
- Portable Equipment

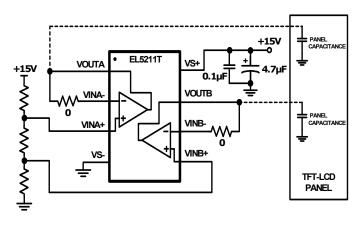


FIGURE 1. TYPICAL TFT-LCD V_{COM} APPLICATION

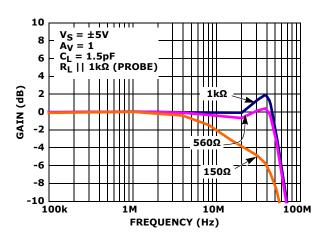
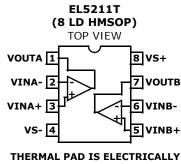
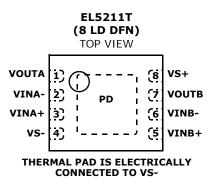


FIGURE 2. FREQUENCY RESPONSE FOR VARIOUS RL

FN6893 Rev 0.00 May 12, 2010

Pin Configuration





CONNECTED TO VS-

Pin Descriptions

PIN NUMBER (HMSOP, DFN)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
1	VOUTA	Amplifier A output	(Reference Circuit 1)
2	VINA-	Amplifier A inverting input	(Reference Circuit 2)
3	VINA+	Amplifier A non-inverting input	(Reference Circuit 2)
4	VS-	Negative power supply	
5	VINB+	Amplifier B non-inverting input	(Reference Circuit 2)
6	VINB-	Amplifier B inverting input	(Reference Circuit 2)
7	VOUTB	Amplifier B output	(Reference Circuit 1)
8	VS+	Positive power supply	
Pad	PD	Functions as a heat sink. Electrically connected to VS Connect the thermal pad to VS- plane on the PCB for optimum thermal performance.	
			V _{S-}
	CIRC	CIRCU	LI 2

Ordering Information

PART NUMBER (Notes 2, 3)	PART MARKING	PACKAGE (Pb-Free)	PKG. DWG. #
EL5211TILZ-T13 (Note 1)	11T	8 Ld DFN	L8.2x3
EL5211TIYEZ	BBBNA	8 Ld HMSOP	MDP0050
EL5211TIYEZ-T7 (Note 1)	BBBNA	8 Ld HMSOP	MDP0050
EL5211TIYEZ-T13 (Note 1)	BBBNA	8 Ld HMSOP	MDP0050

NOTES:

- 1. Please refer to TB347 for details on reel specifications.
- 2. These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matter tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- 3. For Moisture Sensitivity Level (MSL), please see device information page for EL5211T. For more information on MSL please see techbrief TB363.



Absolute Maximum Ratings (T _A = +25°C)	T
Supply Voltage between V_S + and V_S +19.8V Input Voltage Range (V_{INX+} , V_{INX-}) V_S 0.5V, V_S + + 0.5V Input Differential Voltage (V_{INX+} - V_{INX-})	Tŀ
$\begin{array}{llllllllllllllllllllllllllllllllllll$	St Ar Ma
Human Body Model	Po

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ _{JC} (°C/W)
8 Ld HMSOP (Notes 4, 5)	. 62	13
8 Ld DFN (Notes 4, 5)	. 58	8
Storage Temperature	-6 5°	C to +150°C
Ambient Operating Temperature	40	0°C to +85°C
Maximum Junction Temperature		+150°C
Power Dissipation	See Figur	es 34 and 35
Pb-Free Reflow Profile	S	ee link below
http://www.intersil.com/pbfree/Pb-	-FreeReflow.	asp

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- 4. θ_{JA} is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. See Tech Brief TB379.
- 5. For θ_{JC} , the "case temp" location is the center of the exposed metal pad on the package underside.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$

PARAMETER	DESCRIPTION	CONDITIONS	MIN	ТҮР	MAX	UNIT
INPUT CHAR	ACTERISTICS				1	<u>.</u>
V _{OS}	Input Offset Voltage	$V_{CM} = OV$		5	18	mV
TCV _{OS}	Average Offset Voltage Drift (Note 6)	8 Ld HMSOP package		13		µV/°C
		8 Ld DFN package		9		µV/°C
IB	Input Bias Current	$V_{CM} = OV$		2	60	nA
R _{IN}	Input Impedance			1		GΩ
C _{IN}	Input Capacitance			2		pF
CMIR	Common-Mode Input Range		-5.5		+5.5	V
CMRR	Common-Mode Rejection Ratio	For V _{IN} from -5.5V to 5.5V	50	73		dB
A _{VOL}	Open-Loop Gain	$-4.5V \le V_{OUTx} \le 4.5V$	62	78		dB
OUTPUT CHA	RACTERISTICS		-			
V _{OL}	Output Swing Low	I _L = -5mA		-4.95	-4.85	V
V _{OH}	Output Swing High	$I_L = +5mA$	4.85	4.95		V
I _{SC}	Short-Circuit Current	V_{CM} = 0V, Source: V_{OUTx} short to V_{S^-} , Sink: V_{OUTx} short to V_{S^+}		±300		mA
I _{OUT}	Output Current			±65		mA
POWER SUPP				-		•
$(V_{S}+) - (V_{S}-)$	Supply Voltage Range		4.5		19	V
I _S	Supply Current	$V_{CM} = 0V$, No load		5.5	7.5	mA
PSRR	Power Supply Rejection Ratio	Supply is moved from $\pm 2.25V$ to $\pm 9.5V$	60	75		dB
DYNAMIC PE	RFORMANCE					
SR	Slew Rate (Note 7)	$-4.0V \le V_{OUTx} \le 4.0V$, 20% to 80%		100		V/µs
t _S	Settling to +0.1% (Note 8)	$ \begin{array}{l} A_V = \ +1, \ V_{OUTx} = 2V \ step, \\ R_L = \ 1k\Omega \parallel 1k\Omega \ (probe), \ C_L = \ 1.5 pF \end{array} $		85		ns
BW	-3dB Bandwidth	$R_L = 1k\Omega, C_L = 1.5pF$		60		MHz

Electrical Specifications $V_{S^+} = +5V$, $V_{S^-} = -5V$, $R_L = 1k\Omega$ to 0V, $T_A = +25^{\circ}C$, Unless Otherwise Specified.



Electrical Specifications $V_{S^+} = +5V$, $V_{S^-} = -5V$, $R_L = 1k\Omega$ to 0V, $T_A = +25^{\circ}C$, Unless Otherwise Specified. (Continued)							
PARAMETER	DESCRIPTION	CONDITIONS	MIN	ТҮР	MAX	UNIT	
GBWP	Gain-Bandwidth Product	$ \begin{array}{l} A_V = \ \text{-10, } R_F = \ 1 k \Omega, R_G = \ 100 \Omega \\ R_L = \ 1 k \Omega \parallel 1 k \Omega \ (\text{probe}), \ C_L = \ 1.5 pF \end{array} $		32		MHz	
PM	Phase Margin	$ \begin{array}{l} A_V = \ \text{-10, } R_F = \ 1 k \Omega, R_G = \ 100 \Omega \\ R_L = \ 1 k \Omega \parallel 1 k \Omega \ (\text{probe}), \ C_L = \ 1.5 \text{pF} \end{array} $		50		o	
CS	Channel Separation	f = 5MHz		90		dB	

 $\label{eq:constraint} \textbf{Electrical Specifications} \quad \textbf{V}_{S^+} = +5 \textbf{V}, \ \textbf{V}_{S^-} = 0 \textbf{V}, \ \textbf{R}_L = 1 \textbf{k} \Omega \ \text{to} \ 2.5 \textbf{V}, \ \textbf{T}_A = +25 ^\circ \textbf{C}, \ \text{Unless Otherwise Specified}.$

PARAMETER	DESCRIPTION	CONDITION	MIN	ТҮР	MAX	UNIT
INPUT CHAR	ACTERISTICS				1	
V _{OS}	Input Offset Voltage	$V_{CM} = 2.5V$		5	18	mV
TCV _{OS}	Average Offset Voltage Drift (Note 6)	8 Ld HMSOP package		11		µV/°C
		8 Ld DFN package		8		µV/°C
Ι _Β	Input Bias Current	$V_{CM} = 2.5V$		2	60	nA
R _{IN}	Input Impedance			1		GΩ
C _{IN}	Input Capacitance			2		pF
CMIR	Common-Mode Input Range		-0.5		+5.5	V
CMRR	Common-Mode Rejection Ratio	For V _{IN} from -0.5V to 5.5V	45	68		dB
A _{VOL}	Open-Loop Gain	$0.5V \le V_{OUTx} \le 4.5V$	62	82		dB
OUTPUT CHA	RACTERISTICS					
V _{OL}	Output Swing Low	$I_L = -4.2 \text{mA}$		60	150	mV
V _{OH}	Output Swing High	$I_L = +4.2 \text{mA}$	4.85	4.94		V
I _{SC}	Short-circuit Current	V_{CM} = 2.5V, Source: V_{OUTx} short to $V_{S^{-}}$, Sink: V_{OUTx} short to $V_{S^{+}}$		±110		mA
I _{OUT}	Output Current			±65		mA
POWER SUPP	PLY PERFORMANCE					
$(V_{S}+) - (V_{S}-)$	Supply Voltage Range		4.5		19	V
I _S	Supply Current	$V_{CM} = 2.5V$, No load		6.0	7.5	mA
PSRR	Power Supply Rejection Ratio	Supply is moved from 4.5V to 19V	60	75		dB
DYNAMIC PE	RFORMANCE					
SR	Slew Rate (Note 7)	$1V \le V_{OUTx} \le 4V$, 20% to 80%		75		V/µs
t _S	Settling to +0.1% (Note 8)	$ \begin{array}{l} A_V = +1, \ V_{OUTx} = 2V \ step, \\ R_L = 1 k \Omega \ 1 k \Omega \ (probe), \ C_L = 1.5 pF \end{array} $		90		ns
BW	-3dB Bandwidth	$R_L = 1k\Omega, C_L = 1.5pF$		60		MHz
GBWP	Gain-Bandwidth Product	$ \begin{array}{l} A_V = \ -10, \ R_F = \ 1 k \Omega, \ R_G = \ 100 \Omega \\ R_L = \ 1 k \Omega \parallel 1 k \Omega \ (\text{probe}), \ C_L = \ 1.5 \text{pF} \end{array} $		32		MHz
PM	Phase Margin	$ \begin{array}{l} A_V = -10, \ R_F = 1 k \Omega, R_G = 100 \Omega \\ R_L = 1 k \Omega \parallel 1 k \Omega \ (probe), \ C_L = 1.5 pF \end{array} $		50		0
CS	Channel Separation	f = 5MHz		90		dB

PARAMETER	DESCRIPTION	CONDITION	MIN	ΤΥΡ	MAX	UNIT
INPUT CHAR	ACTERISTICS				1	<u></u>
V _{OS}	Input Offset Voltage	$V_{CM} = 9V$		7	18	mV
TCV _{OS}	Average Offset Voltage Drift (Note 6)	8 Ld HMSOP package		14		µV/°C
		8 Ld DFN package		11		µV/°C
Ι _Β	Input Bias Current	$V_{CM} = 9V$		2	60	nA
R _{IN}	Input Impedance			1		GΩ
C _{IN}	Input Capacitance			2		pF
CMIR	Common-Mode Input Range		-0.5		+18.5	V
CMRR	Common-Mode Rejection Ratio	For V _{IN} from -0.5V to 18.5V	53	75		dB
A _{VOL}	Open-Loop Gain	$0.5V \le V_{OUTx} \le 17.5V$	62	104		dB
OUTPUT CHA	RACTERISTICS					
V _{OL}	Output Swing Low	$I_L = -6mA$		80	150	mV
V _{OH}	Output Swing High	$I_L = +6mA$	17.85	17.92		V
I _{SC}	Short-circuit Current	V_{CM} = 9V, Source: V_{OUTx} short to V_{S} -, Sink: V_{OUTx} short to V_{S} +		±300		mA
I _{OUT}	Output Current			±65		mA
POWER SUPP	LY PERFORMANCE					
$(V_{S}^{+}) - (V_{S}^{-})$	Supply Voltage Range		4.5		19	V
I _S	Supply Current	$V_{CM} = 9V$, No load		6.0	7.5	mA
PSRR	Power Supply Rejection Ratio	Supply is moved from 4.5V to 19V	60	75		dB
DYNAMIC PE	RFORMANCE					-
SR	Slew Rate (Note 7)	$1V \le V_{OUTx} \le 17V$, 20% to 80%		100		V/µs
t _S	Settling to +0.1% (Note 8)	$ \begin{array}{l} A_V = \ + \ 1, \ V_{OUTx} = \ 2 V \ step, \\ R_L = \ 1 k \Omega \parallel 1 k \Omega \ (probe), \ C_L = \ 1.5 p F \end{array} $		100		ns
BW	-3dB Bandwidth	$R_{L} = 1k\Omega, C_{L} = 1.5pF$		60		MHz
GBWP	Gain-Bandwidth Product	$ \begin{array}{l} A_V = \ -10, \ R_F = \ 1k\Omega, \ R_G = \ 100\Omega \\ R_L = \ 1k\Omega \parallel 1k\Omega \ (probe), \ C_L = \ 1.5pF \end{array} $		32		MHz
РМ	Phase Margin			50		0
CS	Channel Separation	f = 5MHz		90		dB

NOTES:

6. Measured over -40°C to +85°C ambient operating temperature range. See the typical TCV_{OS} production distribution shown in the "Typical Performance Curves" on page 6.

7. Typical slew rate is an average of the slew rates measured on the rising (20% to 80%) and the falling (80% to 20%) edges of the output signal.

8. Settling time measured as the time from when the output level crosses the final value on rising/falling edge to when the output level settles within a $\pm 0.1\%$ error band. The range of the error band is determined by: Final Value(V) \pm [Full Scale(V) * 0.1%].



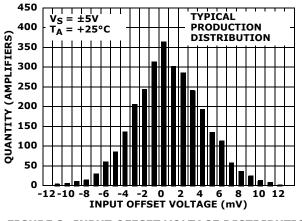


FIGURE 3. INPUT OFFSET VOLTAGE DISTRIBUTION

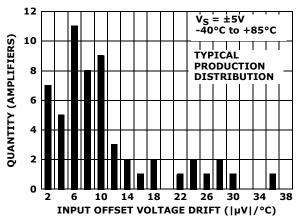


FIGURE 5. INPUT OFFSET VOLTAGE DRIFT (DFN)

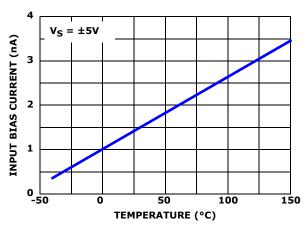


FIGURE 7. INPUT BIAS CURRENT vs TEMPERATURE

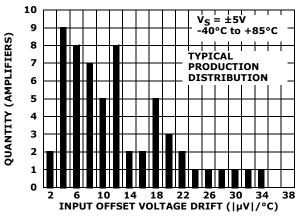


FIGURE 4. INPUT OFFSET VOLTAGE DRIFT (HMSOP)

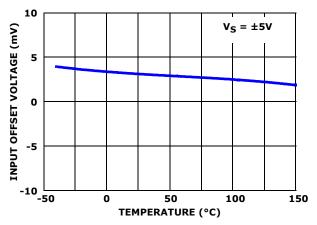


FIGURE 6. INPUT OFFSET VOLTAGE vs TEMPERATURE

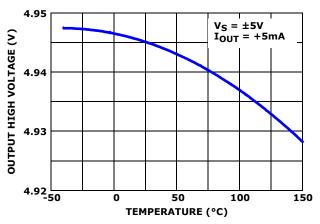


FIGURE 8. OUTPUT HIGH VOLTAGE vs TEMPERATURE



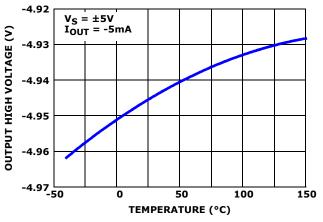


FIGURE 9. OUTPUT LOW VOLTAGE vs TEMPERATURE

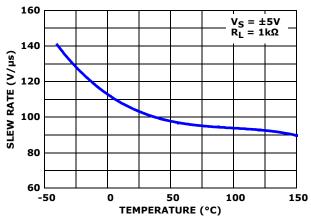
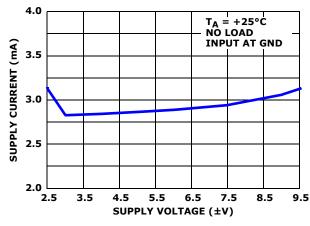


FIGURE 11. SLEW RATE vs TEMPERATURE





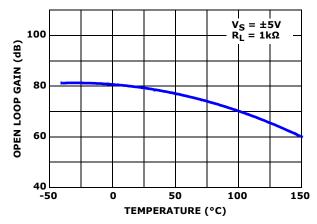


FIGURE 10. OPEN-LOOP GAIN vs TEMPERATURE

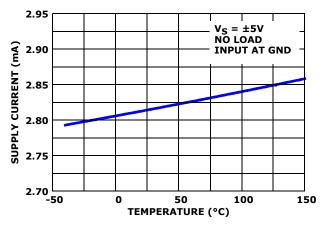
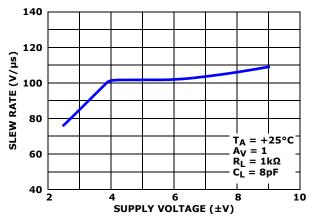


FIGURE 12. SUPPLY CURRENT PER AMPLIFIER vs TEMPERATURE





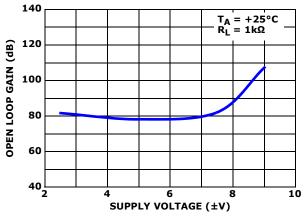
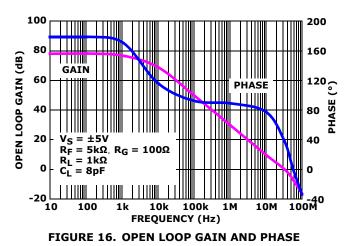


FIGURE 15. OPEN LOOP GAIN vs SUPPLY VOLTAGE



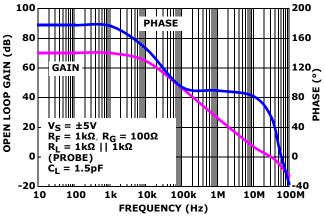


FIGURE 17. OPEN LOOP GAIN AND PHASE

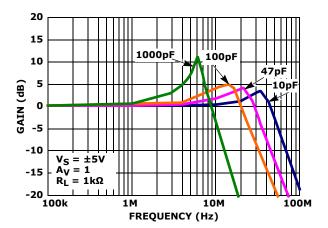


FIGURE 19. FREQUENCY RESPONSE FOR VARIOUS CL

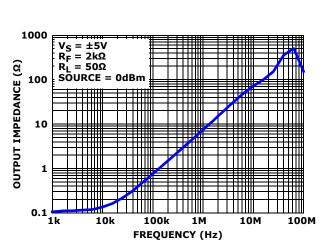
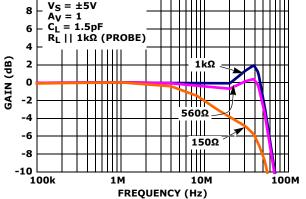
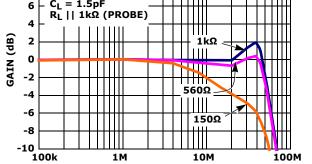


FIGURE 20. CLOSED LOOP OUTPUT IMPEDANCE

FIGURE 18. FREQUENCY RESPONSE FOR VARIOUS RL



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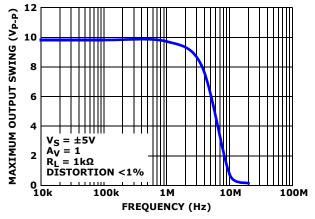


FIGURE 21. MAXIMUM OUTPUT SWING vs FREQUENCY

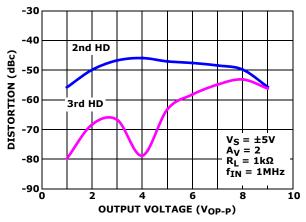
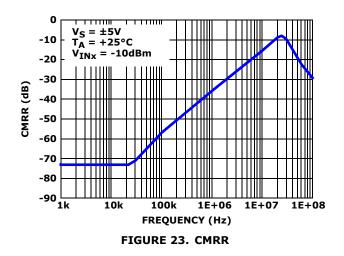
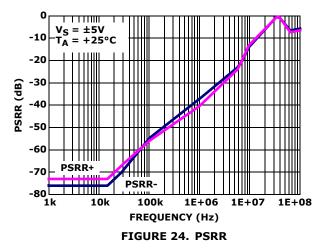
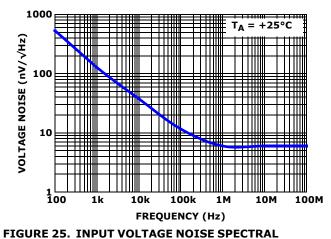
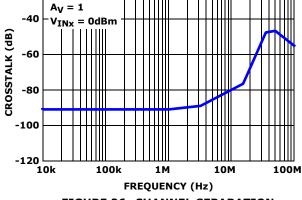


FIGURE 22. HARMONIC DISTORTION vs VOP-P







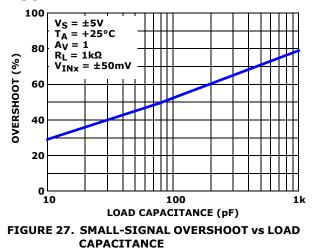


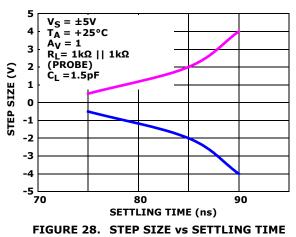
DENSITY

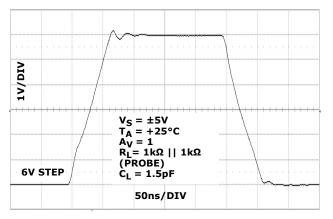
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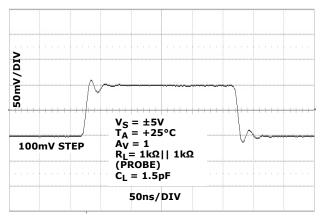
 $V_S = \pm 5V$



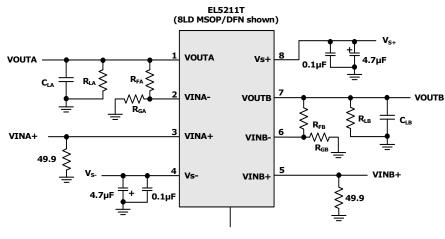












THERMAL PAD CONNECTED TO V_s-





Applications Information

Product Description

The EL5211T is a high voltage rail-to-rail input-output amplifier with low power consumption. The EL5211T contains four amplifiers. Each amplifier exhibits beyond the rail input capability, rail-to-rail output capability and is unity gain stable.

The EL5211T features a high slew rate of 100V/µs, and fast settling time. Also, the device provides common mode input capability beyond the supply rails, rail-to-rail output capability, and a bandwidth of 60MHz (-3dB). This enables the amplifiers to offer maximum dynamic range at any supply voltage.

Operating Voltage, Input and Output Capability

The EL5211T can operate on a single supply or dual supply configuration. The EL5211T operating voltage ranges from a minimum of 4.5V to a maximum of 19V. This range allows for a standard 5V (or $\pm 2.5V$) supply voltage to dip to -10%, or a standard 18V (or $\pm 9V$) to rise by +5.5% without affecting performance or reliability.

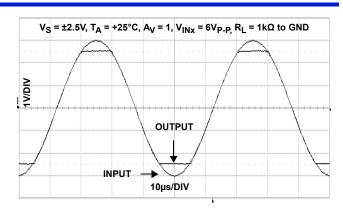
The input common-mode voltage range of the EL5211T extends 500mV beyond the supply rails. Also, the EL5211T is immune to phase reversal. However, if the common mode input voltage exceeds the supply voltage by more than 0.5V, electrostatic protection diodes in the input stage of the device begin to conduct. Even though phase reversal will not occur, to maintain optimal reliability it is suggested to avoid input voltage driven 500mV beyond the supply rails and the device output swinging between the supply rails.

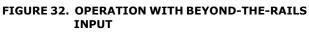
The EL5211T output typically swings to within 50mV of positive and negative supply rails with load currents of \pm 5mA. Decreasing load currents will extend the output voltage range even closer to the supply rails. Figure 33 shows the input and output waveforms for the device in a unity-gain configuration. Operation is from \pm 5V supply with a 1k Ω load connected to GND. The input is a 10V_{P-P} sinusoid and the output voltage is approximately 9.9V_{P-P}.

Refer to the "Electrical Specifications" Table beginning on page 3 for specific device parameters. Parameter variations with operating voltage, loading and/or temperature are shown in the "Typical Performance Curves" on page 6.

Output Current

The EL5211T is capable of output short circuit currents of 300mA (source and sink), and the device has built-in protection circuitry which limits the output current to \pm 300mA (typical).





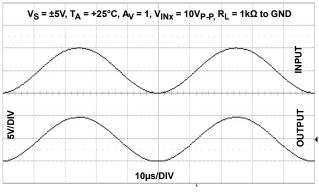


FIGURE 33. OPERATION WITH RAIL-TO-RAIL INPUT AND OUTPUT

To maintain maximum reliability, the continuous output current should never exceed ± 65 mA. This ± 65 mA limit is determined by the characteristics of the internal metal interconnects. Also, see "Power Dissipation" on page 12 for detailed information on ensuring proper device operation and reliability for temperature and load conditions.

Unused Amplifiers

It is recommended that any unused amplifiers be configured as a unity gain follower. The inverting input should be directly connected to the output and the non-inverting input tied to the ground.

Thermal Shutdown

The EL5211T has a built-in thermal protection which ensures safe operation and prevents internal damage to the device due to overheating. When the die temperature reaches +165°C (typical), the device automatically shuts OFF the outputs by putting them in a high impedance state. When the die cools by +15°C (typical), the device automatically turns ON the outputs by putting them in a low impedance (normal) operating state.



Driving Capacitive Loads

As load capacitance increases, the -3dB bandwidth will decrease and peaking can occur. Depending on the application, it may be necessary to reduce peaking and to improve device stability. To improve device stability a snubber circuit or a series resistor may be added to the output of the EL5211T.

A snubber is a shunt load consisting of a resistor in series with a capacitor. An optimized snubber can improve the phase margin and the stability of the EL5211T. The advantage of a snubber circuit is that it does not draw any DC load current or reduce the gain.

Another method to reduce peaking is to add a series output resistor (typically between 1Ω to 10Ω). Depending on the capacitive loading, a small value resistor may be the most appropriate choice to minimize any reduction in gain.

Power Dissipation

With the high-output drive capability of the EL5211T amplifiers, it is possible to exceed the +150°C absolute maximum junction temperature under certain load current conditions. It is important to calculate the maximum power dissipation of the EL5211T in the application. Proper load conditions will ensure that the EL5211T junction temperature stays within a safe operating region.

The maximum power dissipation allowed in a package is determined according to Equation 1:

$$P_{DMAX} = \frac{T_{JMAX} - T_{AMAX}}{\theta_{JA}}$$
(EQ. 1)

where:

- T_{JMAX} = Maximum junction temperature
- T_{AMAX} = Maximum ambient temperature
- Θ_{JA} = Thermal resistance of the package
- P_{DMAX} = Maximum power dissipation allowed

The total power dissipation produced by an IC is the total quiescent supply current times the total power supply voltage, plus the power dissipation in the IC due to the loads, or:

$$\mathsf{P}_{\mathsf{DMAX}} = \Sigma i [\mathsf{V}_{\mathsf{S}} \times \mathsf{I}_{\mathsf{SMAX}} + (\mathsf{V}_{\mathsf{S}} + - \mathsf{V}_{\mathsf{OUT}}i) \times \mathsf{I}_{\mathsf{LOAD}}i] \qquad (\mathsf{EQ.}\ 2)$$

when sourcing, and:

$$\mathsf{P}_{\mathsf{DMAX}} = \Sigma i [\mathsf{V}_{\mathsf{S}} \times \mathsf{I}_{\mathsf{SMAX}} + (\mathsf{V}_{\mathsf{OUT}} i - \mathsf{V}_{\mathsf{S}}^{-}) \times \mathsf{I}_{\mathsf{LOAD}} i] \tag{EQ. 3}$$

when sinking,

where:

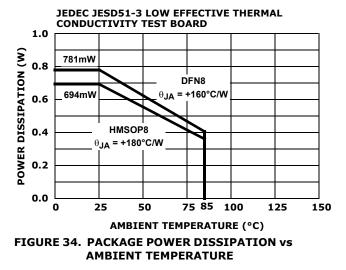
- i = 1 to 2
 - (1, 2 corresponds to Channel A, B respectively)
- V_S = Total supply voltage (V_{S^+} V_{S^-})
- V_S + = Positive supply voltage

- V_S- = Negative supply voltage
- I_{SMAX} = Maximum supply current per amplifier

(I_{SMAX} = EL5211T quiescent current ÷ 2)

- V_{OUT} = Output voltage
- I_{LOAD} = Load current

Device overheating can be avoided by calculating the minimum resistive load condition, R_{LOAD} , resulting in the highest power dissipation. To find R_{LOAD} set the two P_{DMAX} equations equal to each other and solve for V_{OUT}/I_{LOAD} . Reference the package power dissipation curves, Figures 34 and 35, for further information.





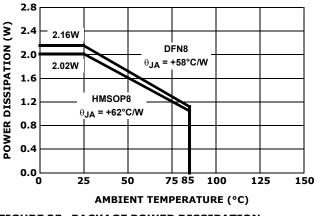


FIGURE 35. PACKAGE POWER DISSIPATION vs AMBIENT TEMPERATURE

Power Supply Bypassing and Printed Circuit Board Layout

The EL5211T can provide gain at high frequency, so good printed circuit board layout is necessary for optimum performance. Ground plane construction is highly recommended, trace lengths should be as short as possible and the power supply pins must be well bypassed to reduce any risk of oscillation.

For normal single supply operation (the V_S- pin is connected to ground) a 4.7 μ F capacitor should be placed from V_S+ to ground, then a parallel 0.1 μ F capacitor should be connected as close to the amplifier as possible. One 4.7 μ F capacitor may be used for multiple devices. For dual supply operation, the same capacitor combination should be placed at each supply pin to ground.

It is highly recommended that EL5211T exposed thermal pad packages should always have the pad connected to the lowest potential, V_S-, to optimize thermal and operating performance. PCB vias should be placed below the device's exposed thermal pad to transfer heat to the V_S- plane and away from the device.

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
5/12/10	FN6893.0	Initial Release.
2/24/10	FN6893.0	Pre-release data sheet submitted for formatting.

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*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: <u>EL5211T</u>

To report errors or suggestions for this datasheet, please go to www.intersil.com/askourstaff

FITs are available from our website at http://rel.intersil.com/reports/search.php

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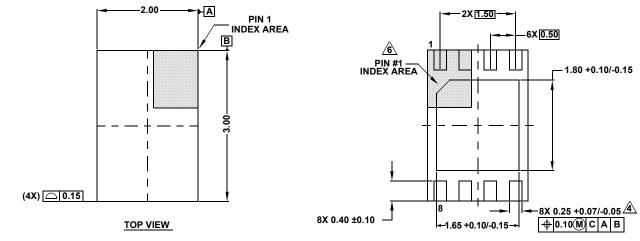
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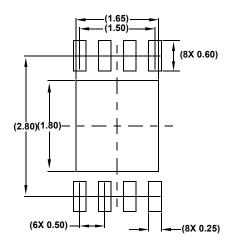
Package Outline Drawing

L8.2x3

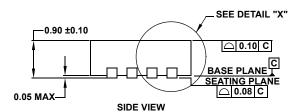
8 LEAD DUAL FLAT NO-LEAD PLASTIC PACKAGE Rev 1, 3/10

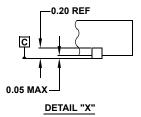


BOTTOM VIEW



TYPICAL RECOMMENDED LAND PATTERN



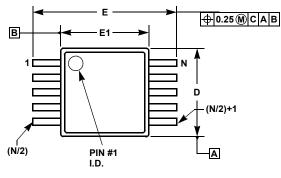


NOTES:

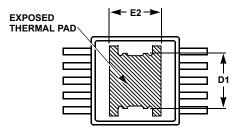
- 1. Dimensions are in millimeters. Dimensions in () for Reference Only.
- 2. Dimensioning and tolerancing conform to ASME Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal ± 0.05
- A Dimension applies to the metallized terminal and is measured between 0.25mm and 0.30mm from the terminal tip.
- 5. Tiebar shown (if present) is a non-functional feature.
- The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
- 7. Compies to JEDEC MO-229 VCED-2.



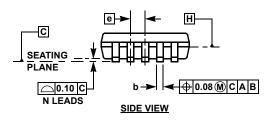
HMSOP (Heat-Sink MSOP) Package Family

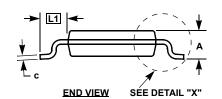


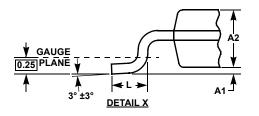




BOTTOM VIEW







MDP0050

HMSOP (HEAT-SINK MSOP) PACKAGE FAMILY

	MILLIN	METERS		
SYMBOL	HMSOP8	HMSOP10	TOLERANCE	NOTES
А	1.00	1.00	Max.	-
A1	0.075	0.075	+0.025/-0.050	-
A2	0.86	0.86	±0.09	-
b	0.30	0.20	+0.07/-0.08	-
С	0.15	0.15	±0.05	-
D	3.00	3.00	±0.10	1, 3
D1	1.85	1.85	Reference	-
E	4.90	4.90	±0.15	-
E1	3.00	3.00	±0.10	2, 3
E2	1.73	1.73	Reference	-
е	0.65	0.50	Basic	-
L	0.55	0.55	±0.15	-
L1	0.95	0.95	Basic	-
Ν	8	10	Reference	-
		•		Rev. 1 2/0

NOTES:

- 1. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25mm maximum per side are not included.
- 3. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994.